## NSN 5961-01-145-6120

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View Online at https://aerobasegroup.com/nsn/5961-01-145-6120 **Inclosure Material:** Metal and glass **Overall Length:** 2.637 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-83 **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 1.031 inches and 1.063 inches **Thread Size:** 0.469 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 600.0 repetitive peak off-state voltage and 3.0 gate trigger voltage, instantaneous **Current Rating Per Characteristic:** 125.00 amperes forward current, total rms pascal and 1400.00 amperes forward current, total rms watts **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0